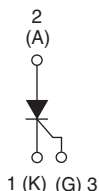




## Surface Mountable Phase Control SCR, 10 A



D<sup>2</sup>PAK



### DESCRIPTION/FEATURES

The 10TTS08SPbF High Voltage Series of silicon controlled rectifiers are specifically designed for medium power switching and phase control applications. The glass passivation technology used has reliable operation up to 125 °C junction temperature.

Typical applications are in input rectification (soft start) and these products are designed to be used with Vishay HPP input diodes, switches and output rectifiers which are available in identical package outlines.

This product has been designed and qualified for industrial level and lead (Pb)-free.



RoHS  
COMPLIANT

### PRODUCT SUMMARY

$V_T$ at 6.5 A	< 1.15 V
$I_{TSM}$	140 A
$V_{RRM}$	800 V

### OUTPUT CURRENT IN TYPICAL APPLICATIONS

APPLICATIONS	SINGLE-PHASE BRIDGE	THREE-PHASE BRIDGE	UNITS
NEMA FR-4 or G-10 glass fabric-based epoxy with 4 oz. (140 µm) copper	2.5	3.5	A
Aluminum IMS, $R_{thCA} = 15$ °C/W	6.3	9.5	
Aluminum IMS with heatsink, $R_{thCA} = 5$ °C/W	14.0	18.5	

#### Note

- $T_A = 55$  °C,  $T_J = 125$  °C, footprint 300 mm<sup>2</sup>

### MAJOR RATINGS AND CHARACTERISTICS

PARAMETER	TEST CONDITIONS	VALUES	UNITS
$I_{T(AV)}$	Sinusoidal waveform	6.5	A
$I_{RMS}$		10	
$V_{RRM}/V_{DRM}$		800	V
$I_{TSM}$		140	A
$V_T$	6.5 A, $T_J = 25$ °C	1.15	V
dV/dt		150	V/µs
dI/dt		100	A/µs
$T_J$	Range	- 40 to 125	°C

### VOLTAGE RATINGS

PART NUMBER	$V_{RRM}$ , MAXIMUM PEAK REVERSE VOLTAGE V	$V_{DRM}$ , MAXIMUM PEAK DIRECT VOLTAGE V	$I_{RRM}/I_{DRM}$ AT 125 °C mA
10TTS08SPbF	800	800	1.0

# 10TTS08SPbF High Voltage Series

Vishay High Power Products Surface Mountable  
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ABSOLUTE MAXIMUM RATINGS				
PARAMETER	SYMBOL	TEST CONDITIONS	VALUES	UNITS
Maximum average on-state current	$I_{T(AV)}$	$T_C = 112\text{ }^{\circ}\text{C}$ , 180° conduction half sine wave	6.5	A
Maximum RMS on-state current	$I_{T(RMS)}$		10	
Maximum peak, one-cycle, non-repetitive surge current	$I_{TSM}$	10 ms sine pulse, rated $V_{RRM}$ applied, $T_J = 125\text{ }^{\circ}\text{C}$	120	
		10 ms sine pulse, no voltage reapplied, $T_J = 125\text{ }^{\circ}\text{C}$	140	$A^2s$
Maximum $I^2t$ for fusing	$I^2t$	10 ms sine pulse, rated $V_{RRM}$ applied, $T_J = 125\text{ }^{\circ}\text{C}$	72	
		10 ms sine pulse, no voltage reapplied, $T_J = 125\text{ }^{\circ}\text{C}$	100	
Maximum $I^2\sqrt{t}$ for fusing	$I^2\sqrt{t}$	$t = 0.1$ to 10 ms, no voltage reapplied, $T_J = 125\text{ }^{\circ}\text{C}$	1000	$A^2\sqrt{s}$
Maximum on-state voltage drop	$V_{TM}$	6.5 A, $T_J = 25\text{ }^{\circ}\text{C}$	1.15	V
On-state slope resistance	$r_t$	$T_J = 125\text{ }^{\circ}\text{C}$	17.3	$m\Omega$
Threshold voltage	$V_{T(TO)}$		0.85	V
Maximum reverse and direct leakage current	$I_{RM}/I_{DM}$	$T_J = 25\text{ }^{\circ}\text{C}$	0.05	mA
		$T_J = 125\text{ }^{\circ}\text{C}$	1.0	
Typical holding current	$I_H$	Anode supply = 6 V, resistive load, initial $I_T = 1\text{ A}$	30	
Maximum latching current	$I_L$	Anode supply = 6 V, resistive load	50	
Maximum rate of rise of off-state voltage	$dV/dt$	$T_J = 25\text{ }^{\circ}\text{C}$	150	$V/\mu s$
Maximum rate of rise of turned-on current	$dI/dt$		100	$A/\mu s$

TRIGGERING				
PARAMETER	SYMBOL	TEST CONDITIONS	VALUES	UNITS
Maximum peak gate power	$P_{GM}$		8.0	W
Maximum average gate power	$P_{G(AV)}$		2.0	
Maximum peak positive gate current	$+I_{GM}$		1.5	A
Maximum peak negative gate voltage	$-V_{GM}$		10	V
Maximum required DC gate current to trigger	$I_{GT}$	Anode supply = 6 V, resistive load, $T_J = -65\text{ }^{\circ}\text{C}$	20	mA
		Anode supply = 6 V, resistive load, $T_J = 25\text{ }^{\circ}\text{C}$	15	
		Anode supply = 6 V, resistive load, $T_J = 125\text{ }^{\circ}\text{C}$	10	
Maximum required DC gate voltage to trigger	$V_{GT}$	Anode supply = 6 V, resistive load, $T_J = -65\text{ }^{\circ}\text{C}$	1.2	V
		Anode supply = 6 V, resistive load, $T_J = 25\text{ }^{\circ}\text{C}$	1	
		Anode supply = 6 V, resistive load, $T_J = 125\text{ }^{\circ}\text{C}$	0.7	
Maximum DC gate voltage not to trigger	$V_{GD}$	$T_J = 125\text{ }^{\circ}\text{C}$ , $V_{DRM} = \text{Rated value}$	0.2	mA
Maximum DC gate current not to trigger	$I_{GD}$		0.1	

SWITCHING				
PARAMETER	SYMBOL	TEST CONDITIONS	VALUES	UNITS
Typical turn-on time	$t_{gt}$	$T_J = 25\text{ }^{\circ}\text{C}$	0.8	$\mu s$
Typical reverse recovery time	$t_{rr}$	$T_J = 125\text{ }^{\circ}\text{C}$	3	
Typical turn-off time	$t_q$		100	



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THERMAL - MECHANICAL SPECIFICATIONS				
PARAMETER	SYMBOL	TEST CONDITIONS	VALUES	UNITS
Maximum junction and storage temperature range	$T_J, T_{Stg}$		- 40 to 125	°C
Soldering temperature	$T_S$	For 10 s (1.6 mm from case)	240	
Maximum thermal resistance, junction to case	$R_{thJC}$	DC operation	1.5	°C/W
Typical thermal resistance, junction to ambient (PCB mount)	$R_{thJA}^{(1)}$		40	
Approximate weight			2	g
			0.07	oz.
Marking device		Case style D <sup>2</sup> PAK (SMD-220)	10TTS08S	

## Note

<sup>(1)</sup> When mounted on 1" square (650 mm<sup>2</sup>) PCB of FR-4 or G-10 material 4 oz. (140 µm) copper 40 °C/W  
For recommended footprint and soldering techniques refer to application note #AN-994

# 10TTS08SPbF High Voltage Series

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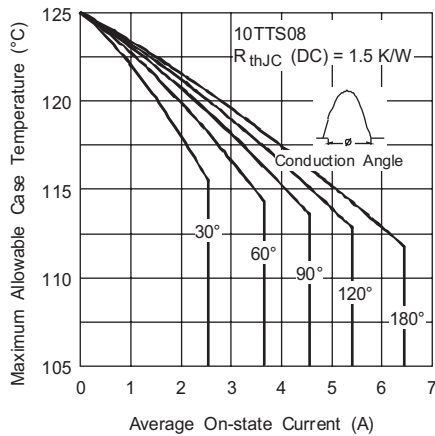


Fig. 1 - Current Rating Characteristics

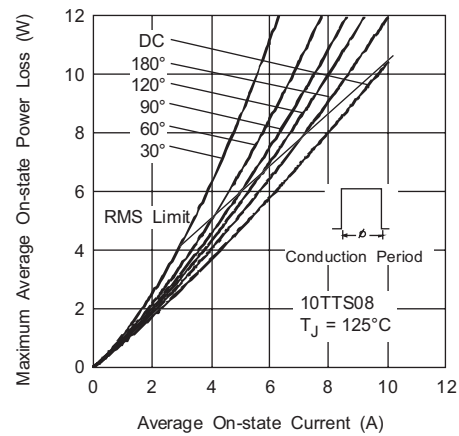


Fig. 4 - On-State Power Loss Characteristics

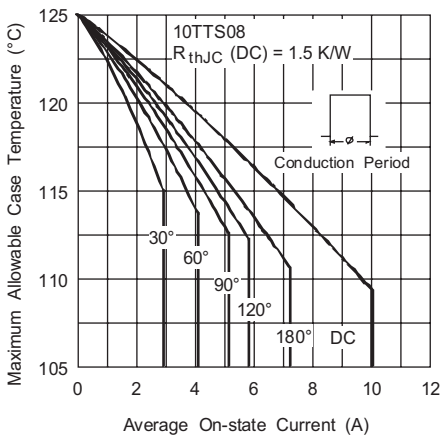


Fig. 2 - Current Rating Characteristics

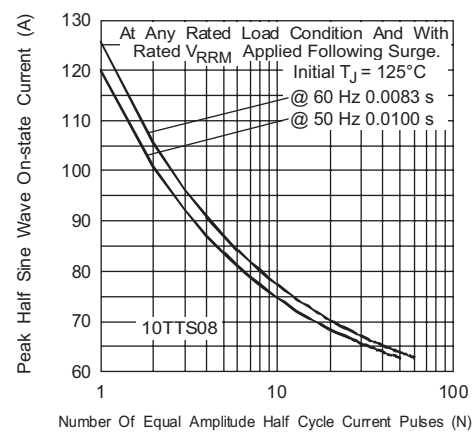


Fig. 5 - Maximum Non-Repetitive Surge Current

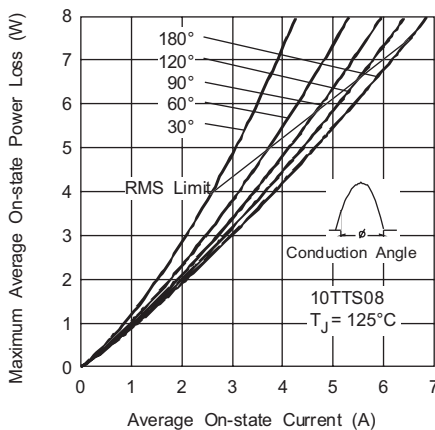


Fig. 3 - On-State Power Loss Characteristics

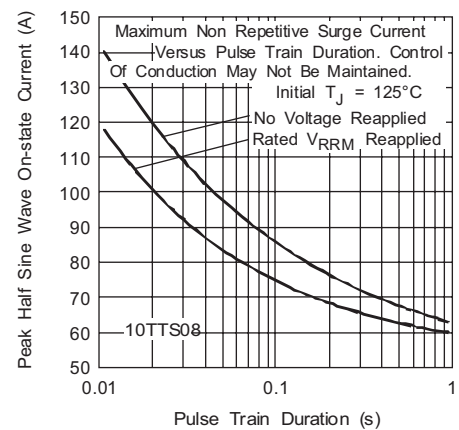


Fig. 6 - Maximum Non-Repetitive Surge Current



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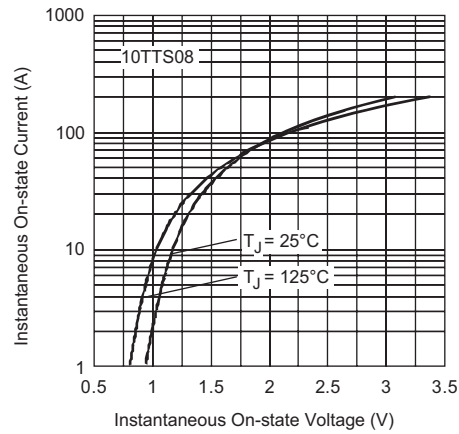


Fig. 7 - On-State Voltage Drop Characteristics

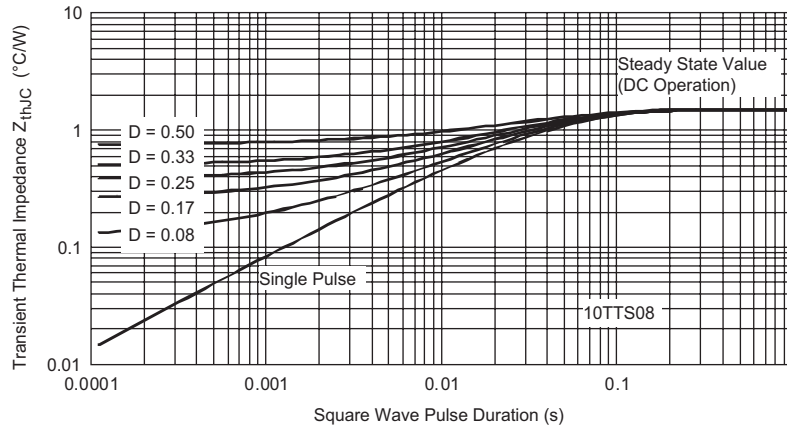


Fig. 8 - Thermal Impedance  $Z_{thJC}$  Characteristics

# 10TTS08SPbF High Voltage Series

Vishay High Power Products      Surface Mountable  
Phase Control SCR, 10 A



## ORDERING INFORMATION TABLE

Device code	10	T	T	S	08	S	TRL	PbF
	1	2	3	4	5	6	7	8

- 1** - Current rating, RMS value
- 2** - Circuit configuration:  
T = Single thyristor
- 3** - Package:  
T = TO-220AC
- 4** - Type of silicon:  
S = Converter grade
- 5** - Voltage code x 100 =  $V_{RRM}$
- 6** - S = TO-220 D<sup>2</sup>PAK (SMD-220) version
- 7** - Tape and reel option:
  - TRL = Left reel
  - TRR = Right orientation reel
- 8** -
  - None = Standard production
  - PbF = Lead (Pb)-free

LINKS TO RELATED DOCUMENTS	
Dimensions	<a href="http://www.vishay.com/doc?95046">http://www.vishay.com/doc?95046</a>
Part marking information	<a href="http://www.vishay.com/doc?95054">http://www.vishay.com/doc?95054</a>
Packaging information	<a href="http://www.vishay.com/doc?95032">http://www.vishay.com/doc?95032</a>



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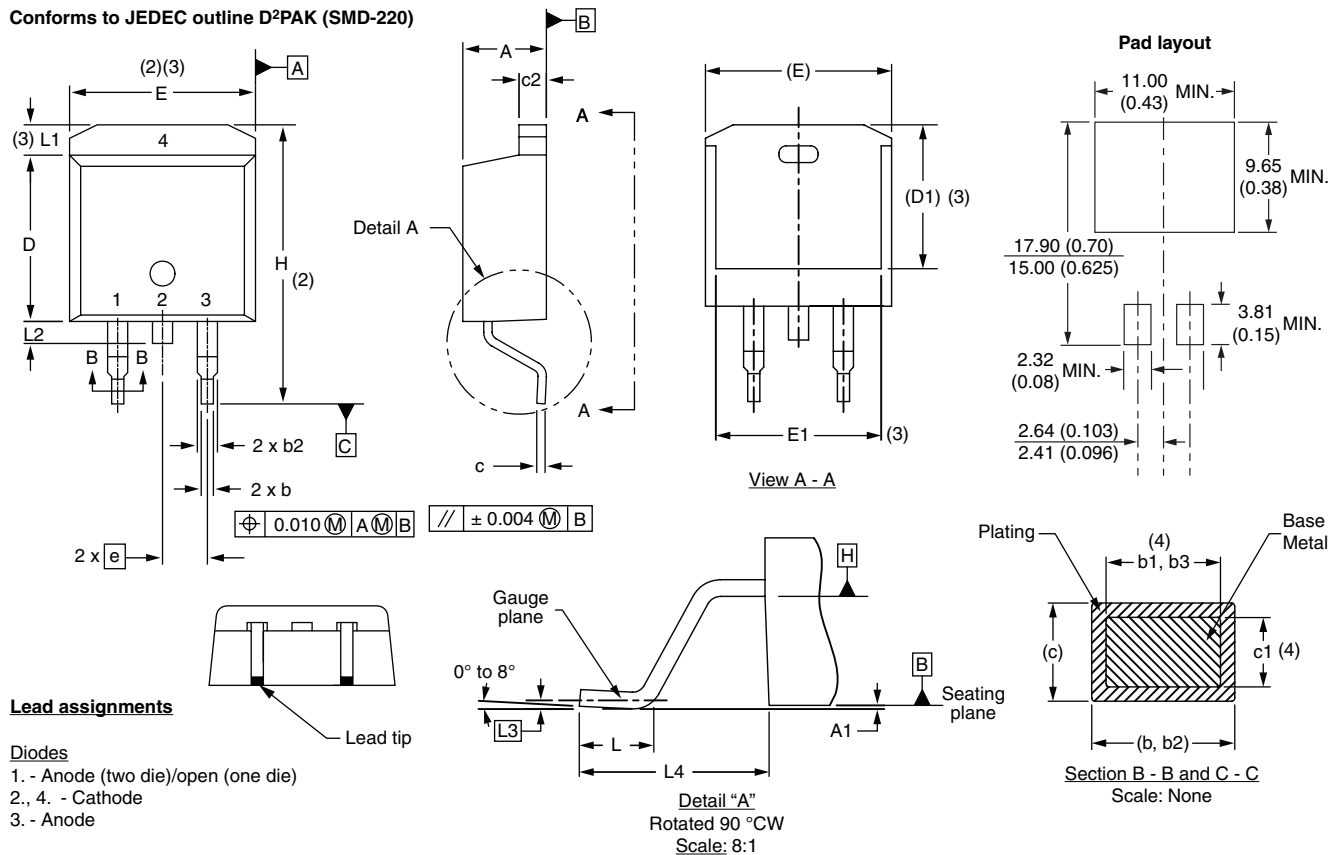
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# D<sup>2</sup>PAK

**DIMENSIONS** in millimeters and inches

**Conforms to JEDEC outline D<sup>2</sup>PAK (SMD-220)**



SYMBOL	MILLIMETERS		INCHES		NOTES	SYMBOL	MILLIMETERS		INCHES		NOTES
	MIN.	MAX.	MIN.	MAX.			MIN.	MAX.	MIN.	MAX.	
A	4.06	4.83	0.160	0.190		D1	6.86	-	0.270	-	3
A1	0.00	0.254	0.000	0.010		E	9.65	10.67	0.380	0.420	2, 3
b	0.51	0.99	0.020	0.039		E1	6.22	-	0.245	-	3
b1	0.51	0.89	0.020	0.035	4	e	2.54 BSC		0.100 BSC		
b2	1.14	1.78	0.045	0.070		H	14.61	15.88	0.575	0.625	
b3	1.14	1.73	0.045	0.068	4	L	1.78	2.79	0.070	0.110	
c	0.38	0.74	0.015	0.029		L1	-	1.65	-	0.066	3
c1	0.38	0.58	0.015	0.023	4	L2	1.27	1.78	0.050	0.070	
c2	1.14	1.65	0.045	0.065		L3	0.25 BSC		0.010 BSC		
D	8.51	9.65	0.335	0.380	2	L4	4.78	5.28	0.188	0.208	

## Notes

- (1) Dimensioning and tolerancing per ASME Y14.5 M-1994
- (2) Dimension D and E do not include mold flash. Mold flash shall not exceed 0.127 mm (0.005") per side. These dimensions are measured at the outmost extremes of the plastic body
- (3) Thermal pad contour optional within dimension E, L1, D1 and E1
- (4) Dimension b1 and c1 apply to base metal only
- (5) Datum A and B to be determined at datum plane H
- (6) Controlling dimension: inch
- (7) Outline conforms to JEDEC outline TO-263AB

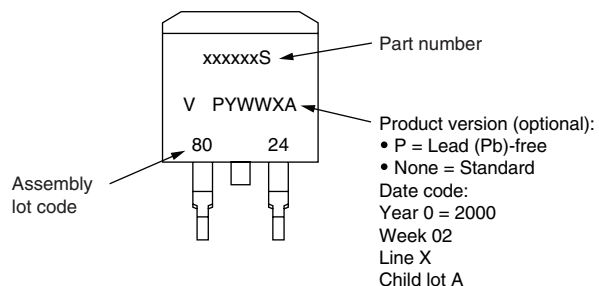




## Part Marking Information

Vishay High Power Products

### D<sup>2</sup>PAK



Example: This is a xxxxxxS with assembly lot code 8024, assembled on WW 02, 2000

## 1